

Advanced Power MOSFET

Features

- High Voltage: $BV_{DSS}=600V(\text{Min.})$
- Low C_{RSS} : $C_{RSS}=7.5pF(\text{Typ.})$
- Low gate charge : $Q_g=16nC(\text{Typ.})$
- Low $R_{DS(on)}$: $R_{DS(on)}=2.5\Omega(\text{Max.})$

Ordering Information

Outline Dimensions

unit : mm



1. Gate
2. Drain
3. Source

STK0460F**Absolute maximum ratings****(Tc=25°C)**

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	600	V
Gate-source voltage	V_{GSS}	±30	V
Drain current (DC)	I_D	(Tc=25°C)	4
		(Tc=100°C)	2.2
Drain current (Pulsed) *	I_{DM}	16	A
Drain Power dissipation	P_D	25	W
Avalanche current (Single) ②	I_{AS}	4	A
Single pulsed avalanche energy ②	E_{AS}	150	mJ
Avalanche current (Repetitive) ①	I_{AR}	4	A
Repetitive avalanche energy ①	E_{AR}	7	mJ
Junction temperature	T_J	150	°C
Storage temperature range	T_{stg}	-55~150	

* Limited by maximum junction temperature

Characteristic		Symbol	Typ.	Max	Unit
Thermal resistance	Junction-case	$R_{th(J-C)}$	-	5.0	°C/W
	Junction-ambient	$R_{th(J-a)}$	-	62.5	

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STK0460F**Electrical Characteristics**

(Tc=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$I_D=250\mu A$, $V_{GS}=0$	600	-	-	V
Gate-threshold voltage	$V_{GS(th)}$	$I_D=250\mu A$, $V_{DS}=V_{GS}$	2.0	-	4.0	V
Drain-source leakage current	I_{DSS}	$V_{DS}=600V$, $V_{GS}=0V$	-	-	1	μA
Gate-source leakage	I_{GSS}	$V_{DS}=0V$, $V_{GS}=\pm 30V$	-	-	± 100	nA
Drain-Source on-resistance ④	$R_{DS(on)}$	$V_{GS}=10V$, $I_D=2.0A$	-	1.9	2.5	Ω
Forward transfer admittance ④	g_{fs}	$V_{DS}=10V$, $I_D=2.0A$	-	3.0	-	S
Input capacitance	C_{iss}	$V_{GS}=0V$, $V_{DS}=25V$, $f=1MHz$	-	520	780	pF
Output capacitance	C_{oss}		-	35	53	
Reverse transfer capacitance	C_{rss}		-	7.5	12	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=300V$, $I_D=4A$ $R_G=25\Omega$ ③④	-	10	-	ns
Rise time	t_r		-	42	-	
Turn-off delay time	$t_{d(off)}$		-	38	-	
Fall time	t_f		-	46	-	
Total gate charge	Q_g	$V_{DS}=300V$, $V_{GS}=10V$ $I_D=4A$ ③④	-	16	24	nC
Gate-source charge	Q_{gs}		-	2.8	4.2	
Gate-drain charge	Q_{gd}		-	5.5	8.3	

Source-Drain Diode Ratings and Characteristics

(Tc=25°C)

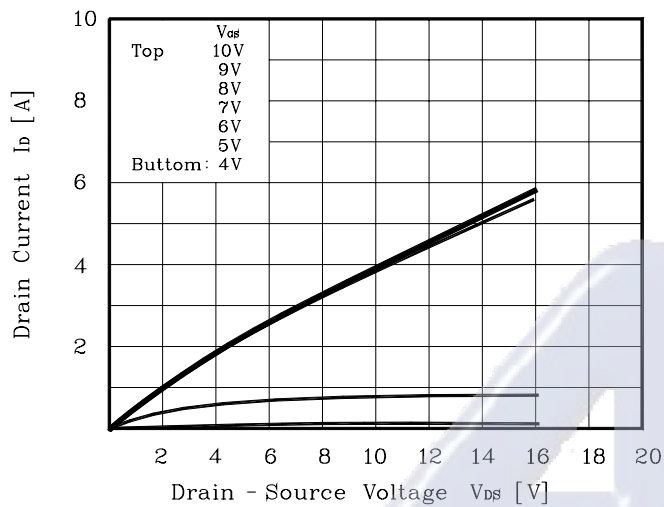
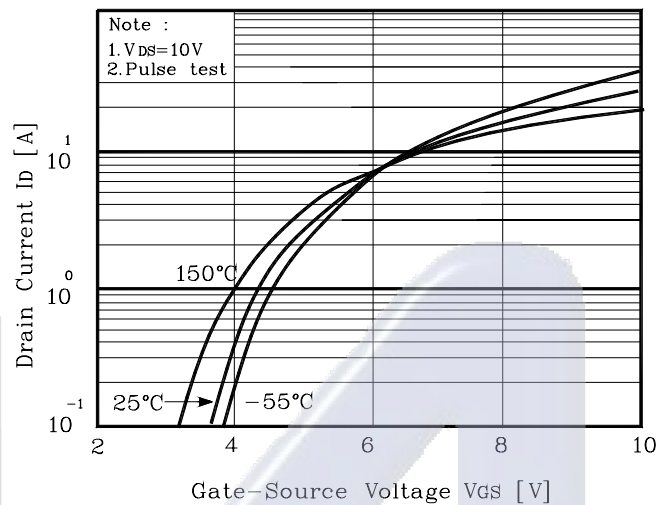
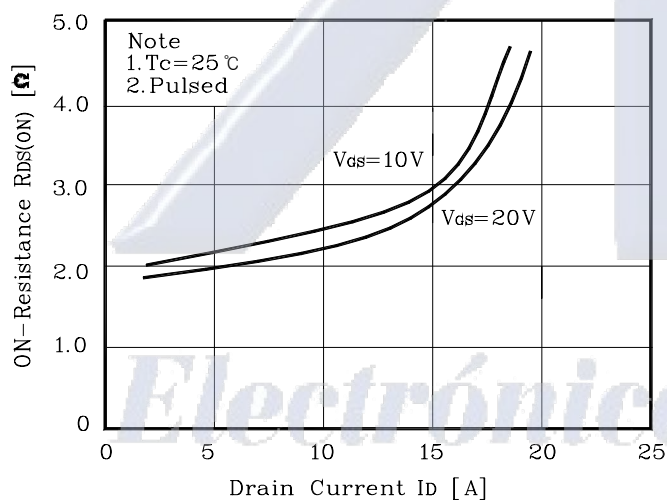
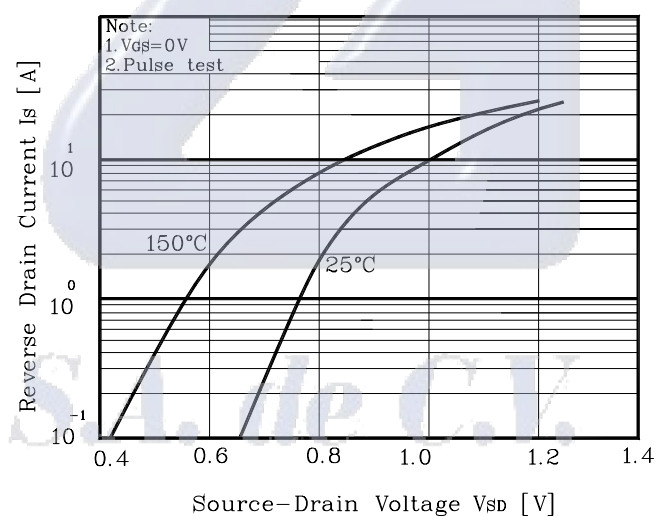
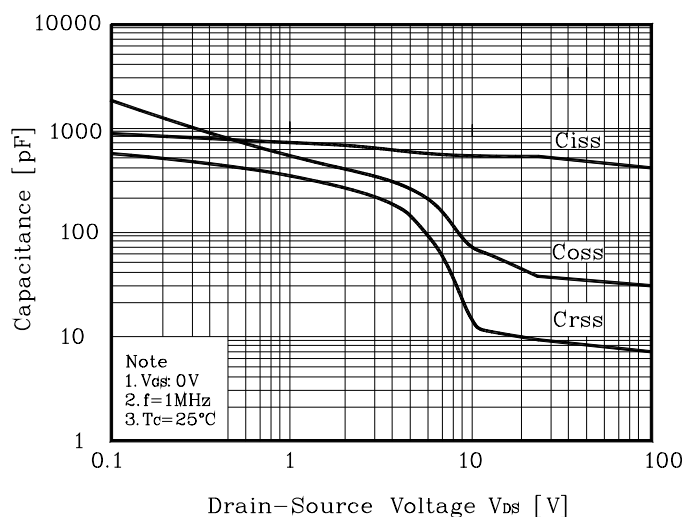
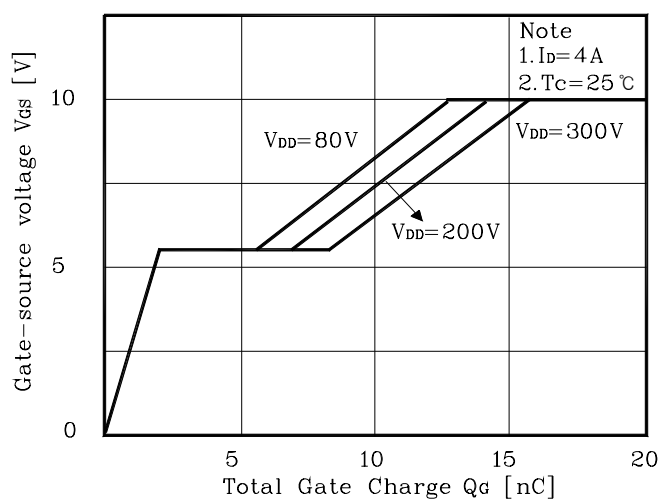
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Continuous source current	I_S	Integral reverse diode in the MOSFET	-	-	4	A
Source current (Pulsed) ①	I_{SM}		-	-	16	
Forward voltage ④	V_{SD}	$V_{GS}=0V$, $I_S=4A$	-	-	1.4	V
Reverse recovery time	t_{rr}	$I_S=4A$	-	310	-	ns
Reverse recovery charge	Q_{rr}	$di_s/dt=100A/us$	-	2.26	-	μC

Note ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② $L=17mH$, $I_{AS}=4A$, $V_{DD}=50V$, $R_G=27\Omega$
- ③ Pulse Test : Pulse Width < 300us, Duty cycle $\leq 2\%$
- ④ Essentially independent of operating temperature

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Electrical Characteristic Curves

Fig. 1 $I_D - V_{DS}$ Fig. 2 $I_D - V_{GS}$ Fig. 3 $R_{DS(on)} - I_D$ Fig. 4 $I_S - V_{SD}$ Fig. 5 Capacitance - V_{DS} Fig. 6 $V_{GS} - Q_G$ 

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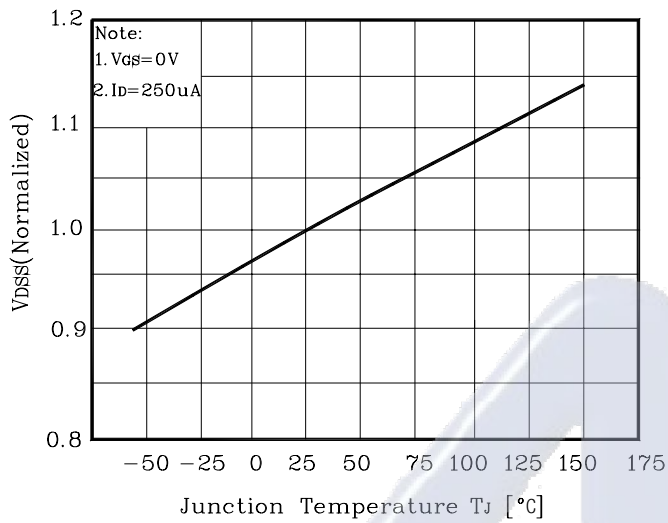
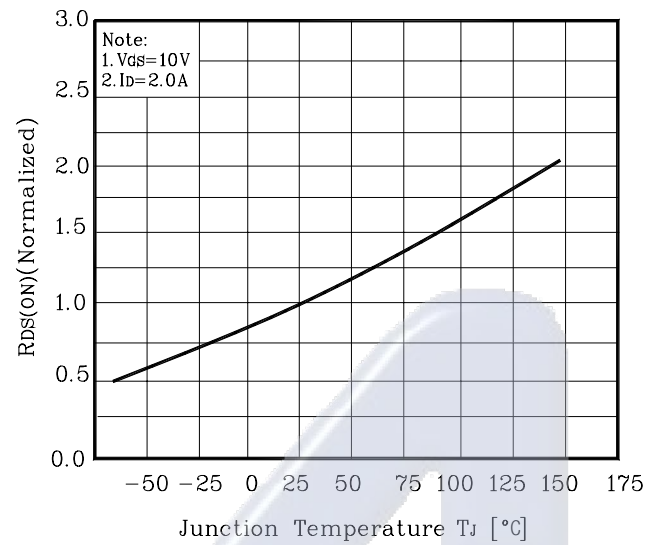
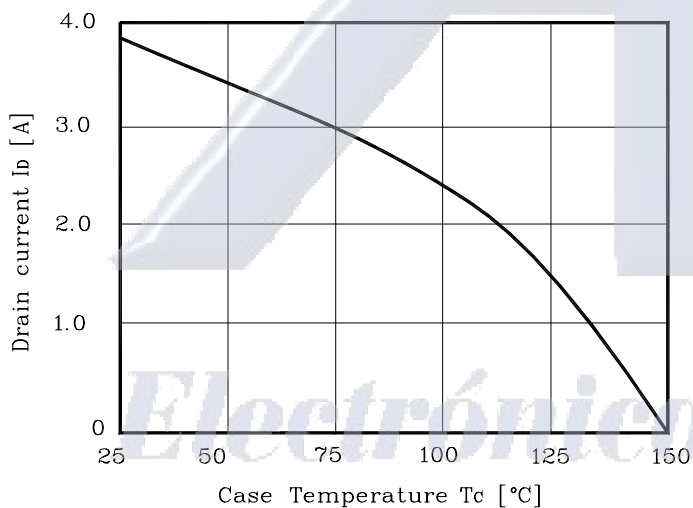
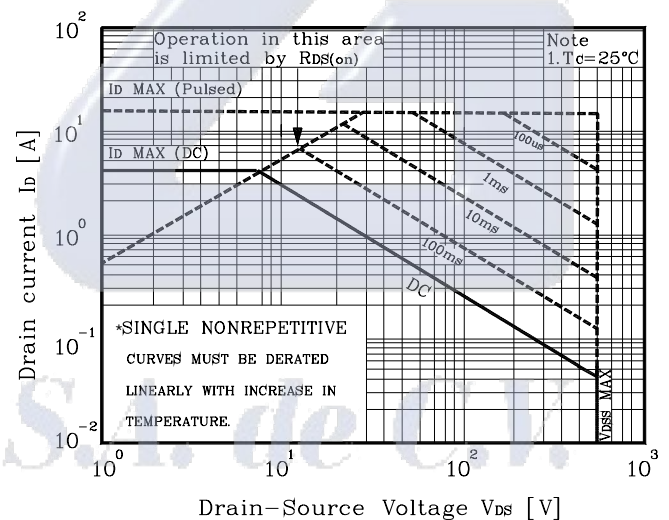
Fig. 7 $V_{DS} - T_J$ Fig. 8 $R_{DS(on)} - T_J$ Fig. 9 $I_D - T_C$ 

Fig. 10 Safe Operating Area



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Fig. 11 Gate Charge Test Circuit & Waveform

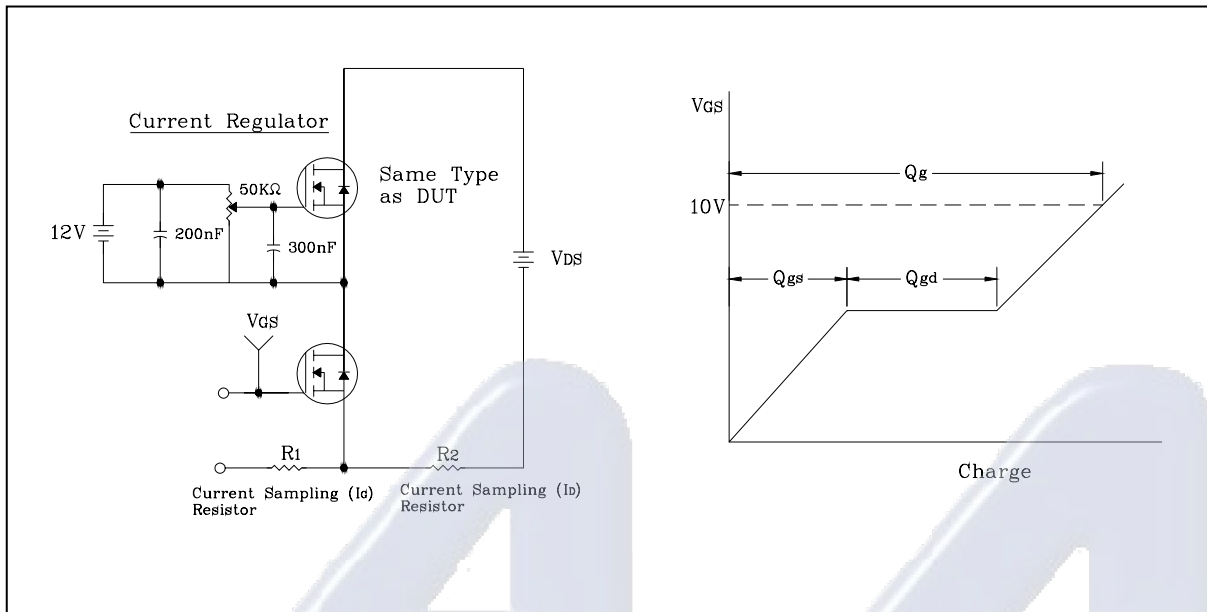


Fig. 12 Resistive Switching Test Circuit & Waveform

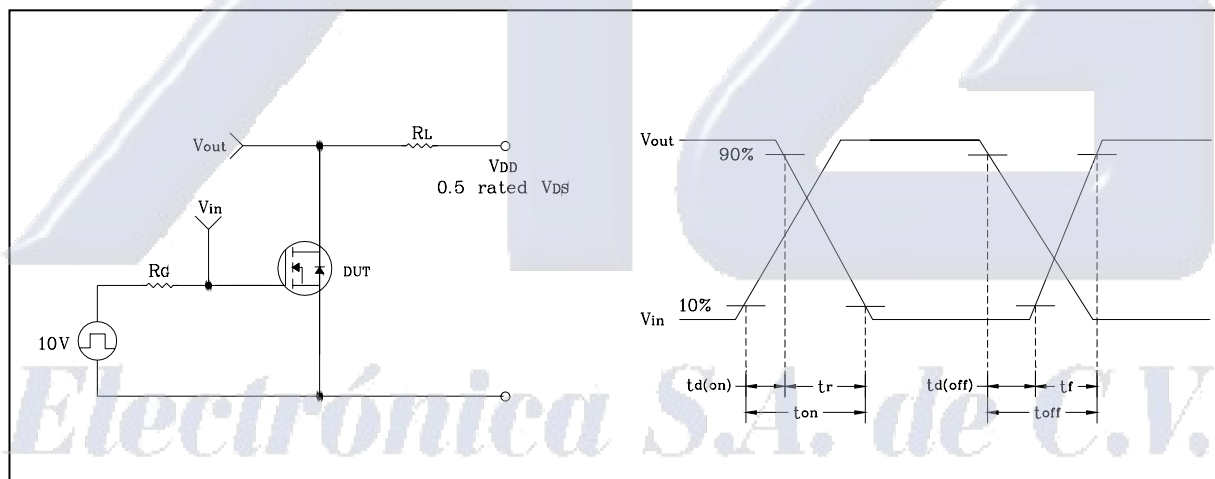
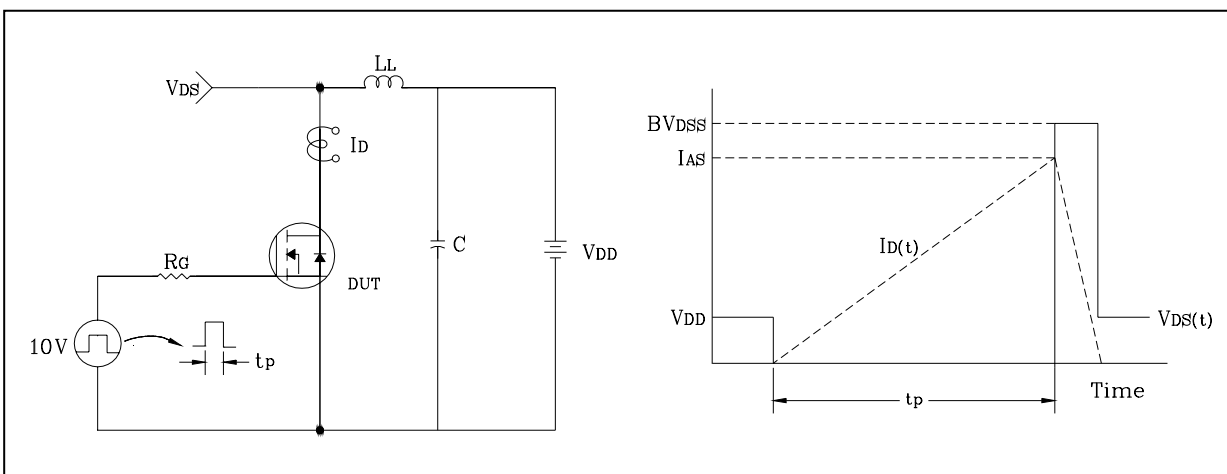
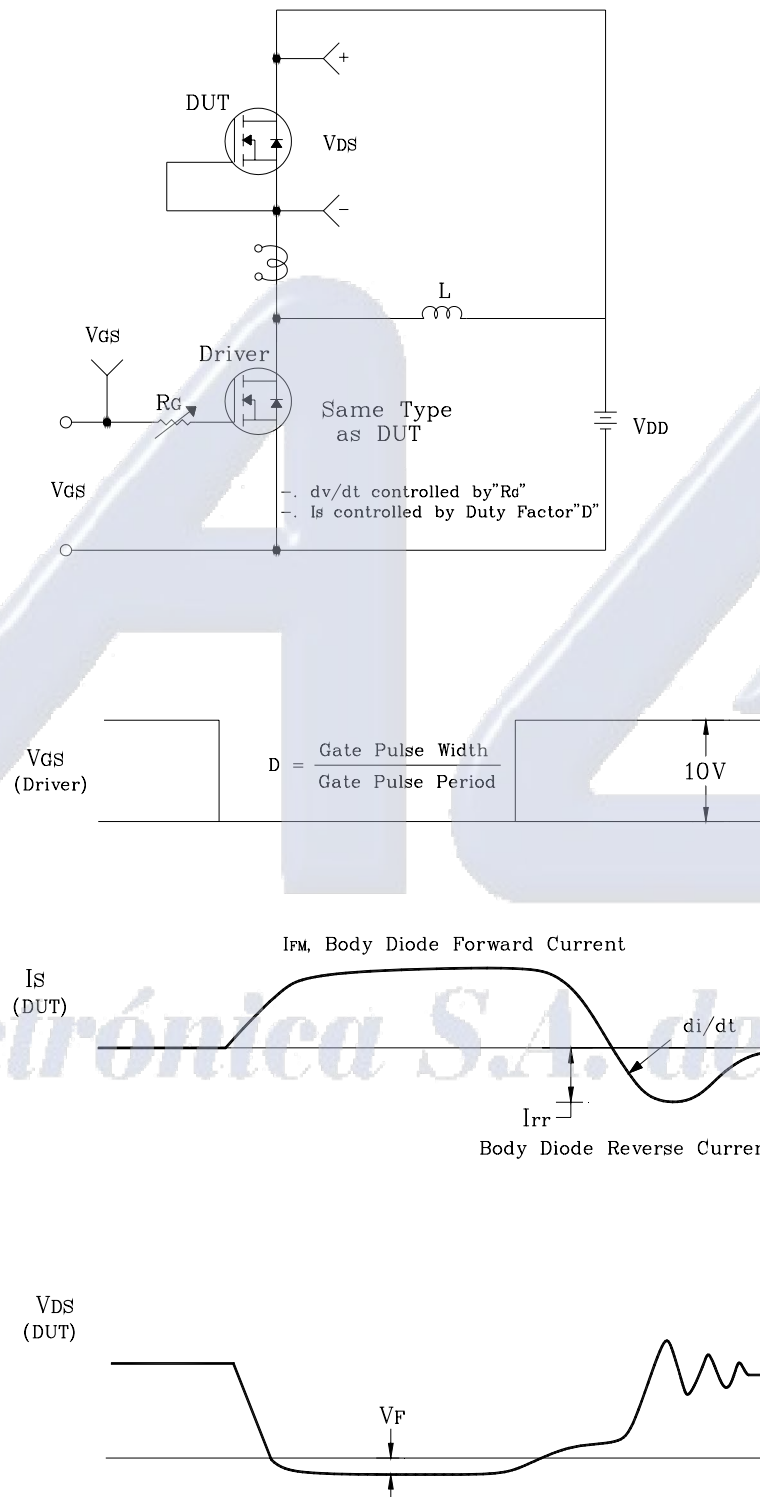


Fig. 13 E_{AS} Test Circuit & Waveform



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Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



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